



JST139E-800D 16A TRIAC

Rev.A.1.1

ELECTRICAL CHARACTERISTICS (unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33$	- -	MAX.	5	mA
				10	
V_{GT}		ALL	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k$	ALL	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	- -	MAX.	15	mA
				20	
I_H	$I_T=500mA$		MAX.	10	mA
dV/dt	$V_D=540V$ Gate Open $T_j=125$		MIN.	40	V s

(dV/dt)_c (dI/dt)_c=7.2A/ms, T

FIG.1: Maximum power dissipation versus RMS on-state current

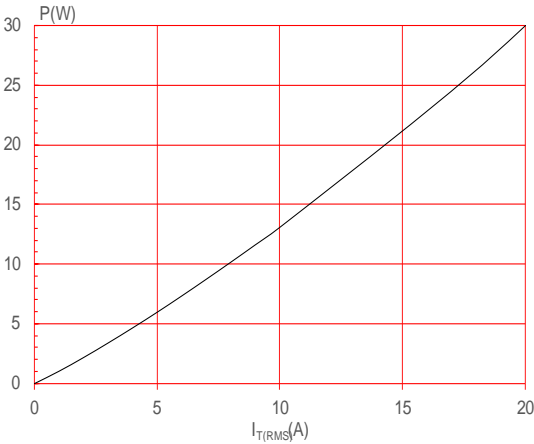


FIG.2: RMS on-state current versus case temperature

FIG.3:

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

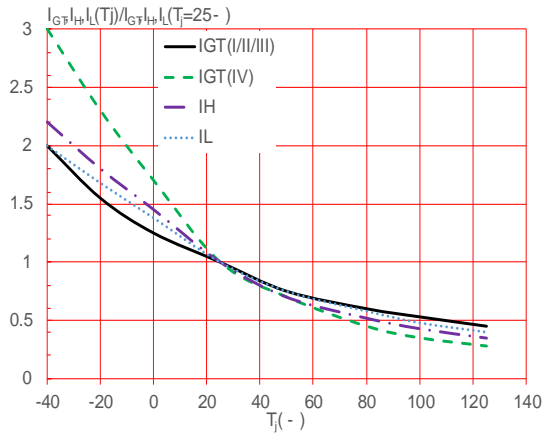


FIG.8: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)		Package	Base qty. (pcs)	Delivery mode
		H- I- J	K			
JST139E-800D	800	5	10	TO-263	50	Tube5 -0.02 Tc 0.02 T

PACKAGE MECHANICAL DATA

DELIVERY MODE



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